LINEAR SYSTEMS

Improved Standard Products®

SD-SST211/213/215

N-CHANNEL LATERAL DMOS SWITCH ZENER PROTECTED

PRODUCT SUMMARY

PART NUMBER	$V_{(BR)DS}$ Min (V)	$V_{(GS)th}$ Max (V)	$r_{DS(on)}$ Max (Ω)	C_{rss} Max (pF)	t_{ON} Max (ns)
SD211DE	30	1.5	45 @ V_{GS}=10V	0.5	2
SD213DE	10	1.5	45 @ V_{GS}=10V	0.5	2
SD215DE	20	1.5	45 @ V_{GS}=10V	0.5	2
SST211	30	1.5	50 @ V_{GS}=10V	0.5	2
SST213	10	1.5	50 @ V_{GS}=10V	0.5	2
SST215	20	1.5	50 @ V_{GS}=10V	0.5	2

Features

- Ultra-High Speed Switching—I_{ON}: 1ns
- Ultra-Low Reverse Capacitance: 0.2pF
- Low Guaranteed r_{DS} @5V
- Low Turn-On Threshold Voltage
- N-Channel Enhancement Mode

Benefits

- High-Speed System Performance
- Low Insertion Loss at High Frequencies
- Low Transfer Signal Loss
- Simple Driver Requirement
- Single Supply Operation

Applications

- Fast Analog Switch
- Fast Sample-and-Holds
- Pixel-Rate Switching
- DAC Deglitchers
- High-Speed Driver

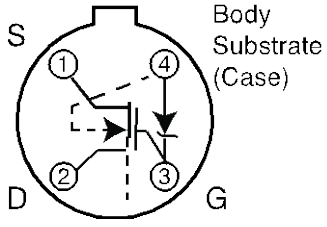
Description

The SD211DE/SST211 series consists of enhancement-mode MOSFETs designed for high speed low-glitch switching in audio, video and high-frequency applications. The SD211 may be used for a ±5-V analog switching or as a high speed driver of the SD214. The SD214 is normally used for ±10-V analog switching. These MOSFETs utilize lateral construction to achieve low capacitance and ultra-fast switching speeds. An integrated ZENER diode provides ESD protection. These devices feature a poly-silicon gate for manufacturing reliability.

For similar products see: quad array—SD5000/5400 series, non-Zener protection—SD210DE/214DE.

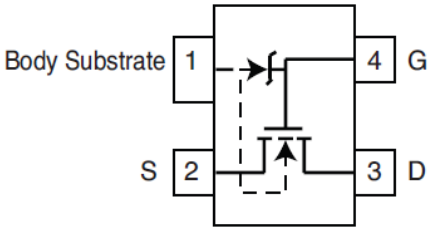
TOP VIEW

SD211DE, SD213DE, SD215DE



TO-206AF
(TO-72)

TO-253
(SOT-143)



TOP VIEW

SST211, SST213, SST215

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Gate Drain, Gate Source Voltage	(SD211DE/SST211) . . . . . -30/25V	Drain-Substrate Voltage	(SD211DE/SST211) 30V
	(SD213DE/SST213). . . . . -15/25V		(SD213DE/SST213) 15V
	(SD215DE/SST215). . . . . -25/30V		(SD215DE/SST215) 25V
Gate-Substrate Voltage[a]	(SD211DE/SST211) . . . . . -0.3/25V	Source-Substrate Voltage	(SD211DE/SST211) 15V
	(SD213DE/SST213) . . . . . -0.3/25V		(SD213DE/SST213) 15V
	(SD215DE/SST215) . . . . . -0.3/30V		(SD215DE/SST215) 25V
Drain-Source Voltage	(SD211DE/SST211) 30V	Drain Current	. . . . . .50mA
	(SD213DE/SST213) 10V	Lead Temperature (1/16" from ease for 10 seconds)	. . . . . 300°C
	(SD215DE/SST215) 20V	Storage Temperature	. . . . . -65 to 150°C
Voltage	(SD211DE/SST211) 10V	Operating Junction Temperature	. . . . . -55 to 125°C
	(SD213DE/SST213) 10V	Power Dissipation	. . . . . .300mW
	(SD215DE/SST215) 20V		

Notes:
a. Derate 3mW/°C above 25°C

Specifications[a]

PARAMETER	SYMBOL[b]	TEST CONDITIONS[b]		TYP[b]	LIMITS 211 Series Min	LIMITS 211 Series Max	LIMITS 213 Series Min	LIMITS 213 Series Max	LIMITS 215 Series Min	LIMITS 215 Series Max	UNIT
Static											
Drain - Source Breakdown Voltage	$V_{(BR)DS}$	V_{GS} = V_{BS} = 0V, I_D = 10 µA		35	30						V
		V_{GS} = V_{BS} = -5V, I_D = 10 nA		30	10		10		20		
Source - Drain Breakdown Voltage	$V_{(BR)SD}$	V_{GS} = V_{BD} = -5V, I_S = 10 nA		22	10		10		20		
Drain - Substrate Breakdown Voltage	$V_{(BR)DBO}$	V_{GB} = 0V, I_D= 10 nA Source Open		35	15		15		25		
Source - Substrate Breakdown Voltage	$V_{(BR)SBO}$	V_{GB} = 0V, I_s = 10 µA Drain Open		35	15		15		25		
Drain – Source Leakage	$I_{DS(off)}$	V_{GS} = V_{BS} = -5V	V_{DS} = 10V	0.4		10		10			nA
			V_{DS} = 20V	0.9						10	
Source - Drain Leakage	$I_{SD(off)}$	V_{GD} = V_{BD} = -5V	V_{SD} = 10V	0.5		10		10			
			V_{SD} = 20V							10	
Gate Leakage	I_{GBS}	V_{DB} = V_{SB} = 0V, V_{GB} = 30V		0.01		100		100		100	
Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1 µA , V_{SB} = 0V		0.8	0.5	1.5	0.1	1.5	0.1	1.5	V
Drain – Source On-Resistance	$r_{DS(on)}$	V_{SB} = 0V I_D = 1mA	V_{GS} = 5V (SD Series)	58		70		70		70	Ω
			V_{GS} = 5V (SST Series)	60		75		75		75	
			V_{GS} = 10V (SD Series)	38		45		45		45	
			V_{GS} = 10V (SST Series)	40		50		50		50	
			V_{GS} = 15V	30							
			V_{GS} = 20V	26							
			V_{GS} = 25V	24							

Specifications[a]

PARAMETER	SYMBOL[b]	TEST CONDITIONS[b]		TYP[c]	LIMITS						UNIT
					211 Series		213 Series		215 Series		
					Min	Max	Min	Max			
Dynamic											
Forward Transconductance	g_{fs}	V_{DS} = 10V, V_{SB} = 0V, , I_D = 20mA, f = 1kHz	SD Series	11	10		10		10		mS
	g_{os}		SST Series	10.5	9		9		9		
			All	0.9							
Gate Node Capacitance	$C_{(GS+GD+GB)}$	V_{DS} = 10V, f = 1MHz V_{GS} = V_{BS} = -15V	SD Series	2.5		3.5		3.5		3.5	pF
Drain Node Capacitance	$C_{(GD+DB)}$			1.1		1.5		1.5		1.5	
Source Node Capacitance	$C_{(GS+SB)}$			3.7		5.5		5.5		5.5	
Reverse Transfer Capacitance	C_{rss}		SST Series	4.2							
			SD Series	0.2		0.5		0.5		0.5	
Switching											
Turn-On Time	$t_{D(on)}$	SD Series Only V_{SB} = 0V, V_{IN} 0 to 5V, R_G = 25Ω V_{DD} = 5V, R_L = 680Ω		0.5		1		1		1	ns
	t_r			0.6		1		1		1	
Turn-Off Time	$t_{D(off)}$			2							
	t_f			6							

Notes:

a. T_A = 25°C unless otherwise notes.

b. B is the body (substrate) and $V_{(BR)}$ is breakdown voltage.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

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